

a dual-terminated transmission line, wherein the dual-terminated transmission line communicatively couples the Direct RAC of first integrated circuit with the Direct RAC of the second integrated circuit.

12. (Once amended) The apparatus of claim 1 [11], wherein impedance of the first metal line is substantially equal to impedance of the second metal line.

15. (Once amended) The apparatus of claim 1 [10], wherein the third integrated circuit comprises a Rambus™ in-line memory module communicatively coupled to the connector.

19. (Once amended) A method of making an article, comprising:  
providing a first integrated circuit having a communication module;  
providing a connector having a first line and a second line, wherein the first line and the second line are communicatively coupled to the first integrated circuit, and wherein the second line is longer than the first line, has a capacitance value greater than a capacitance value of the first line, and impedance of the second line is approximately equal to impedance of the first line;  
providing a second integrated circuit have a communication module; and  
forming a dual-terminated transmission line to couple the first integrated circuit to the second integrated circuit.

**CLEAN VERSION OF CLAIMS FOR SCANNING PER 37 CFR § 1.121****1. An apparatus comprising:**

a first integrated circuit comprising a Direct Rambus™ ASIC Cell (Direct RAC);

a second integrated circuit comprising a Direct RAC;

A1 a mezzanine card having a connector and comprising the second integrated circuit, wherein the connector is adapted to be communicatively coupled to a third integrated circuit, wherein the connector includes a first metal line and a second metal line, the second metal line being longer than the first metal line, and wherein the second metal line has a parasitic capacitance value greater than a parasitic capacitance value of the first metal line; and

a dual-terminated transmission line, wherein the dual-terminated transmission line communicatively couples the Direct RAC of first integrated circuit with the Direct RAC of the second integrated circuit.

A2 1012. The apparatus of claim 1, wherein impedance of the first metal line is substantially equal to impedance of the second metal line.

A3 1318. The apparatus of claim 1, wherein the third integrated circuit comprises a Rambus™ in-line memory module communicatively coupled to the connector.

A4 1718. A method of making an article, comprising:

providing a first integrated circuit having a communication module;

providing a connector having a first line and a second line, wherein the first line and the second line are communicatively coupled to the first integrated circuit,

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and wherein the second line is longer than the first line, has a capacitance value greater than a capacitance value of the first line, and impedance of the second line is approximately equal to impedance of the first line;

providing a second integrated circuit have a communication module; and forming a dual-terminated transmission line to couple the first integrated circuit to the second integrated circuit.

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